



STD20NE06

N - CHANNEL ENHANCEMENT MODE " SINGLE FEATURE SIZE™ " POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD20NE06	60 V	< 0.040 Ω	20 A

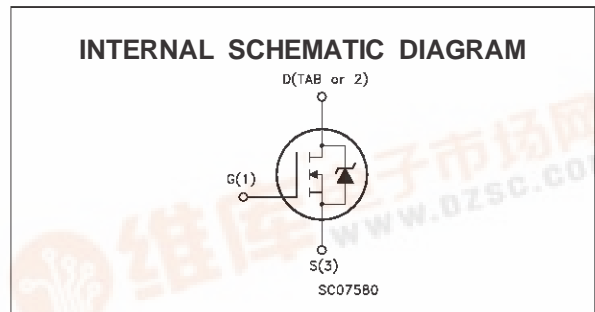
- TYPICAL R_{DS(on)} = 0.032 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION
- FOR THROUGH-HOLE VERSION CONTACT SALES OFFICE

DESCRIPTION

This Power MOSFET is the latest development of SGS-THOMSON unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC CONVERTERS
- AUTOMOTIVE ENVIRONMENT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	60	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	20**	A
I _D	Drain Current (continuous) at T _c = 100 °C	17	A
I _{DM} (•)	Drain Current (pulsed)	80	A
P _{tot}	Total Dissipation at T _c = 25 °C	50	W
	Derating Factor	0.33	W/°C
dv/dt	Peak Diode Recovery voltage slope	7	V/ns
T _{stg}	Storage Temperature	-65 to 175	°C
T _j	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(**) Value limited only by the package

(1) I_{SD} ≤ 36 A, di/dt ≤ 300 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

STD20NE06

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.0	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	100	°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ	1.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		275	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	20	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	80	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _c = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V I _D = 10 A		0.032	0.04	Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V	20			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 10 A	7	13		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		2115	2800	pF
C _{oss}	Output Capacitance			260	350	pF
C _{rss}	Reverse Transfer Capacitance			65	90	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 30\text{ V}$ $I_D = 18\text{ A}$		28	40	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		85	115	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 48\text{ V}$ $I_D = 36\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$		250		A/ μ s
Q_g	Total Gate Charge	$V_{DD} = 48\text{ V}$ $I_D = 36\text{ A}$ $V_{GS} = 10\text{ V}$		50	70	nC
Q_{gs}	Gate-Source Charge			13		nC
Q_{gd}	Gate-Drain Charge			18		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 48\text{ V}$ $I_D = 36\text{ A}$		12	16	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		25	35	ns
t_c	Cross-over Time			40	55	ns

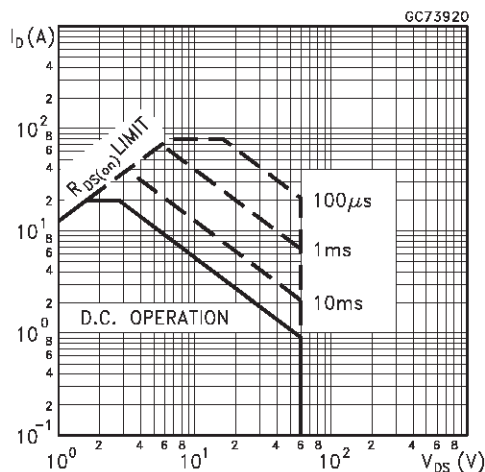
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				20	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				80	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 20\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 36\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		75		ns
Q_{rr}	Reverse Recovery Charge			245		nC
I_{RRM}	Reverse Recovery Current			6.5		A

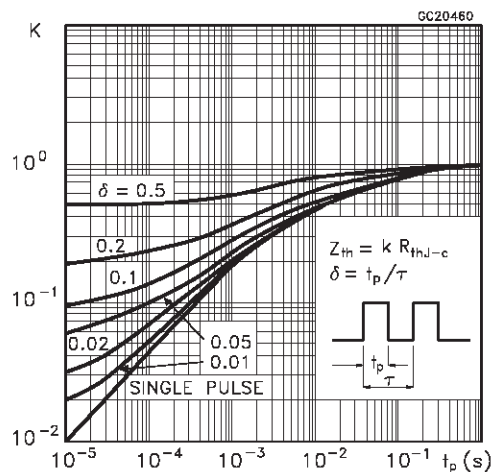
(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(\bullet) Pulse width limited by safe operating area

Safe Operating Area

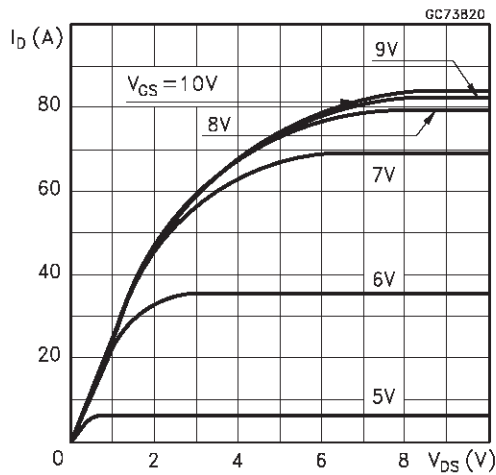


Thermal Impedance

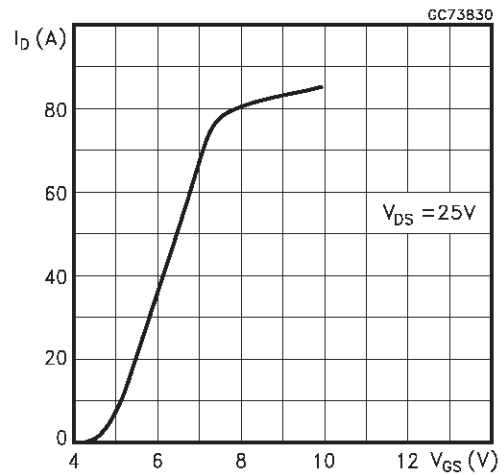


STD20NE06

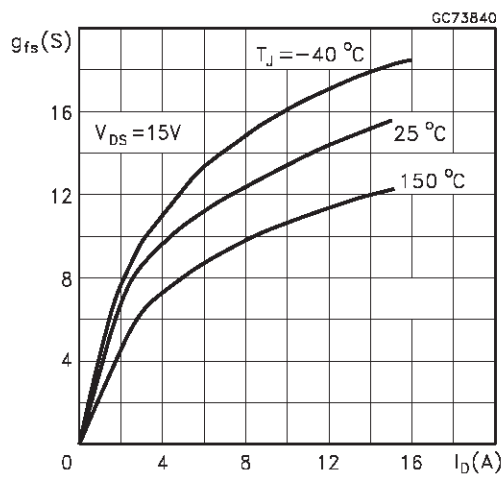
Output Characteristics



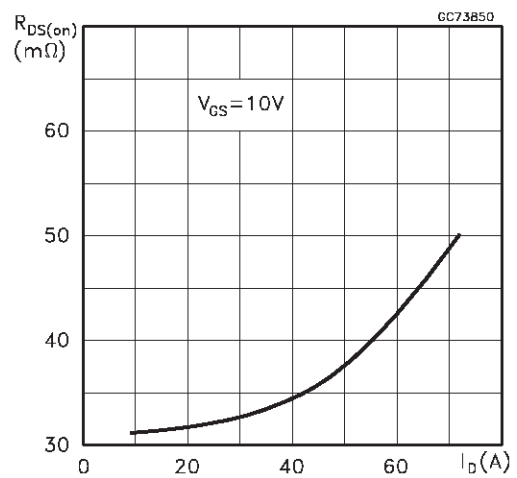
Transfer Characteristics



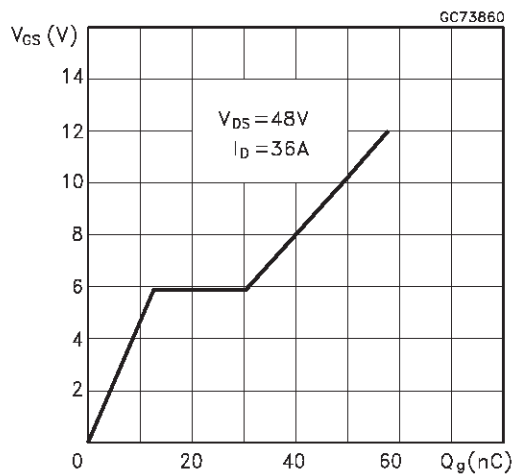
Transconductance



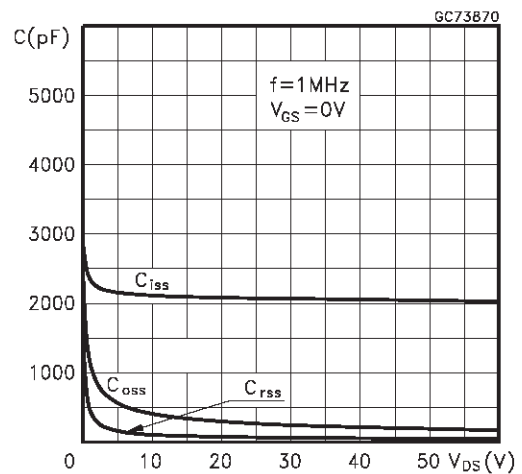
Static Drain-source On Resistance



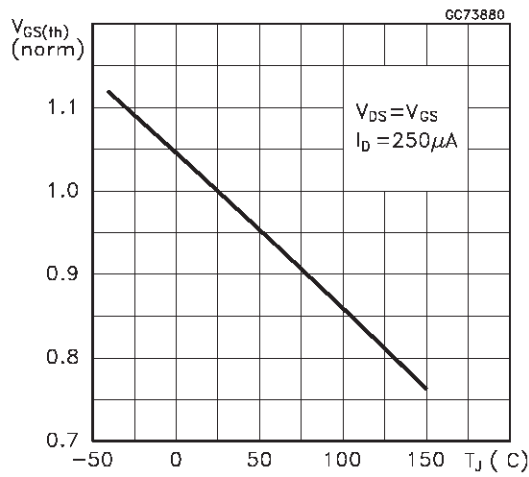
Gate Charge vs Gate-source Voltage



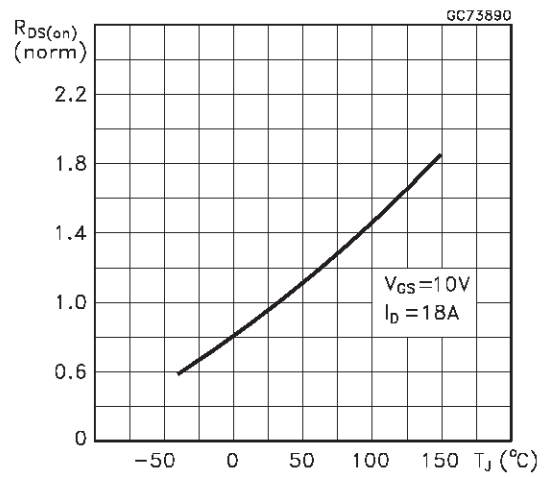
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

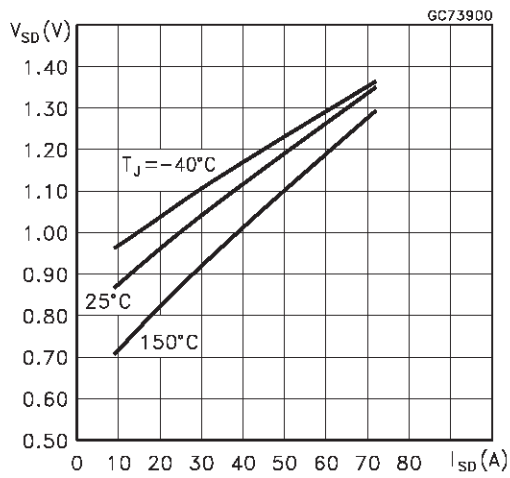


Fig. 1: Unclamped Inductive Load Test Circuit

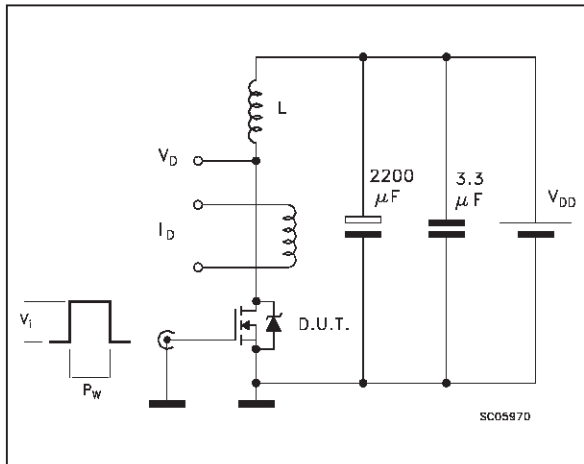


Fig. 2: Unclamped Inductive Waveform

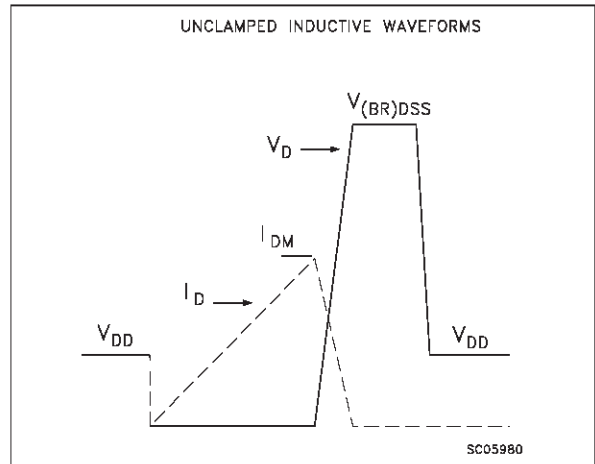


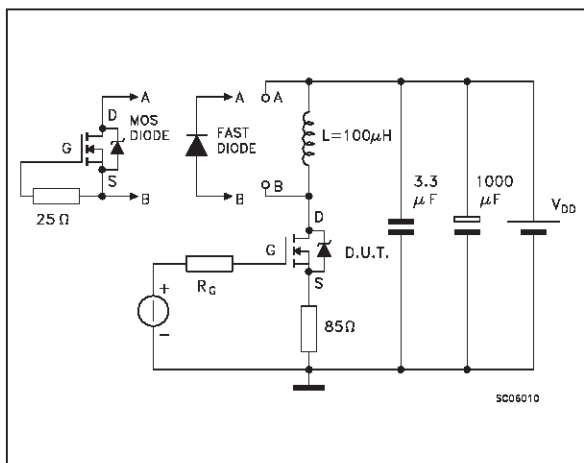
Fig. 3: Switching Times Test Circuits For Resistive Load



Fig. 4: Gate Charge test Circuit

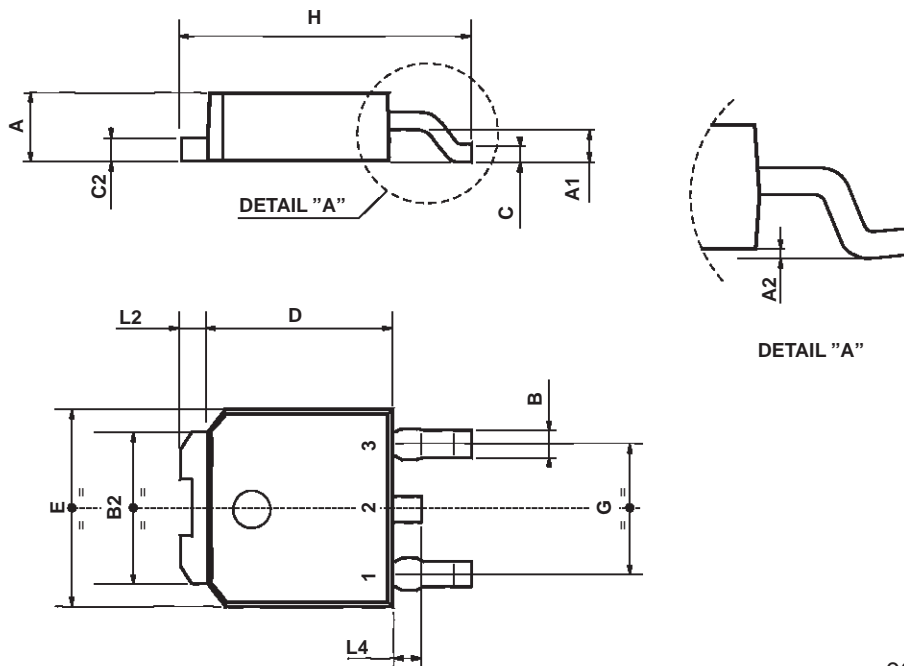


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L2		0.8			0.031	
L4	0.6		1	0.023		0.039



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